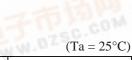
2SD655 WWW.DZSC.COM Silicon NPN Epitaxial REJ03G0768-0200 (Previous ADE-208-1136) Rev.2.00 Aug.10.2005 WWW.DZSC.CO Application Low frequency power amplifier, Muting Outline RENESAS Package code: PRSS0003DA-A (Package name: TO-92 (1)) 1. Emitter WWW.DZSC.COM 2. Collector 2

Absolute Maximum Ratings

| | | | (1a - 23C) |
|------------------------------|----------------------|-------------|------------|
| Item | Sym <mark>bol</mark> | Ratings | Unit |
| Collector to base voltage | V _{CBO} | 30 | V |
| Collector to emitter voltage | V _{CEO} | 15 | V |
| Emitter to base voltage | V _{EBO} | 5 | V |
| Collector current | Ic | 0.7 | А |
| Collector peak current | i _{C(peak)} | 1.0 | А |
| Collector power dissipation | Pc | 500 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | –55 to +150 | °C CO |



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Electrical Characteristics

 $(Ta = 25^{\circ}C)$

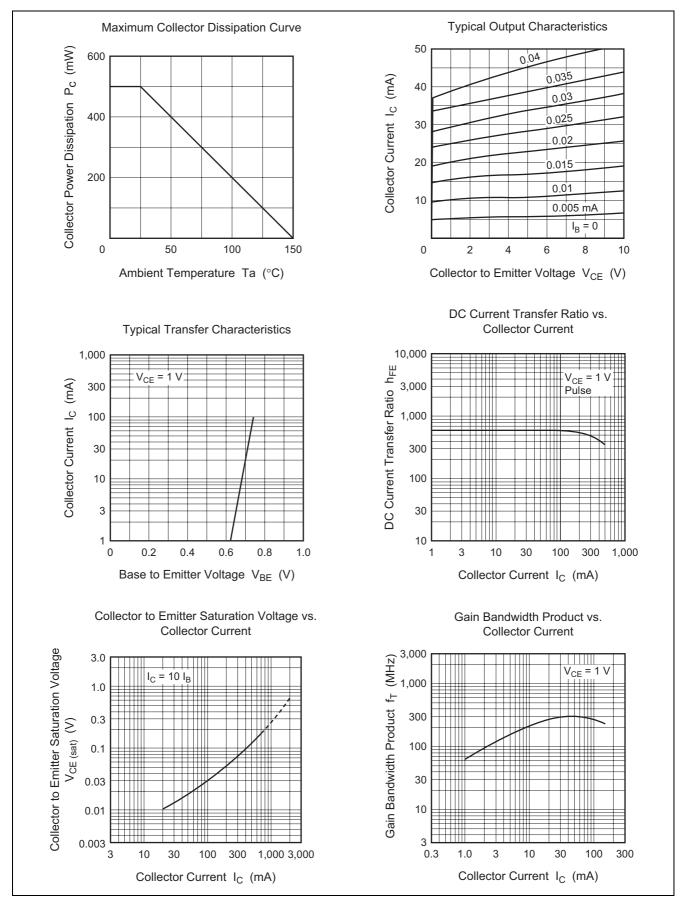
| ltem | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|--------------------------------|-----|------|------|------|--|
| Collector to base breakdown voltage | V _{(BR)CBO} | 30 | — | - | V | $I_{C} = 10 \ \mu A, \ I_{E} = 0$ |
| Collector to emitter breakdown voltage | V _{(BR)CEO} | 15 | — | | V | $I_C = 1 \text{ mA}, R_{BE} = \infty$ |
| Emitter to base breakdown voltage | V _{(BR)EBO} | 5 | — | | V | $I_E = 10 \ \mu A, \ I_C = 0$ |
| Collector cutoff current | I _{CBO} | — | — | 1.0 | μA | $V_{CB} = 20 \text{ V}, I_E = 0$ |
| Base to emitter voltage | V _{BE} | — | — | 1.0 | V | $V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}$ |
| Collector to emitter saturation voltage | V _{CE(sat)} | — | 0.15 | 0.5 | V | $I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}*^2$ |
| DC current transfer ratio | h _{FE} * ¹ | 250 | _ | 1200 | | $V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$ |
| Gain bandwidth product | f⊤ | | 250 | — | MHz | $V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}$ |

Notes: 1. The 2SD655 is grouped by h_{FE} as follows.

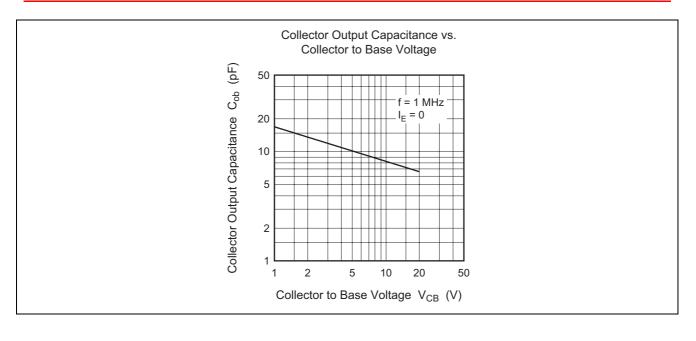
2. Pulse test

| D | ш | F | |
|------------|------------|-------------|--|
| 250 to 500 | 400 to 800 | 600 to 1200 | |

Main Characteristics

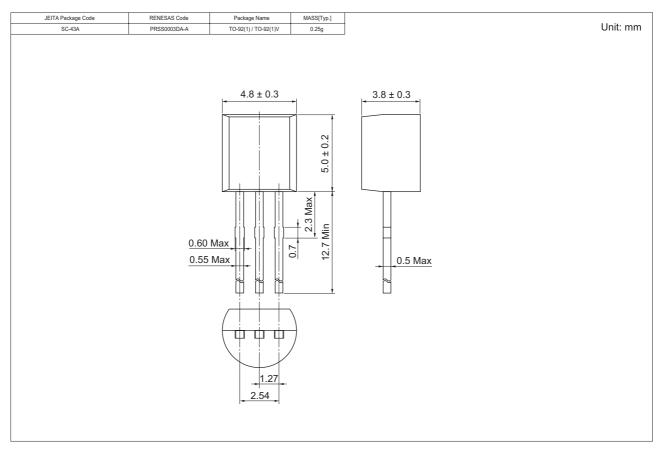


2SD655



2SD655

Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|-------------|----------|-------------------------|
| 2SD655DTZ-E | 2500 | Hold Box, Radial Taping |
| 2SD655ETZ-E | | |
| 2SD655FTZ-E | | |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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